Darlington Transistor

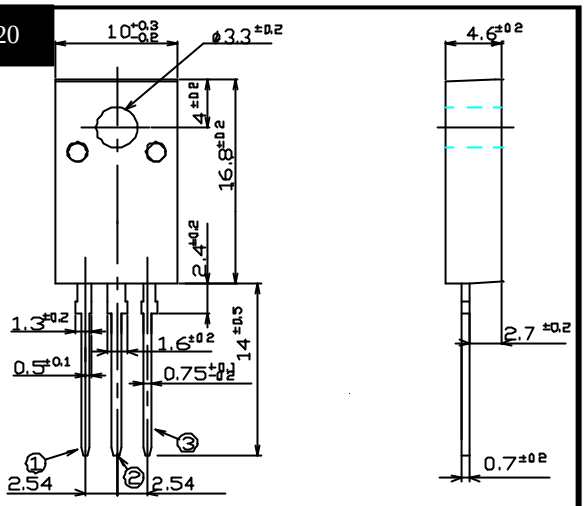
2SB1283
(TP7J10)

-7A PNP

OUTLINE DIMENSIONS

Case : ITO-220

Unit : mm



RATINGS

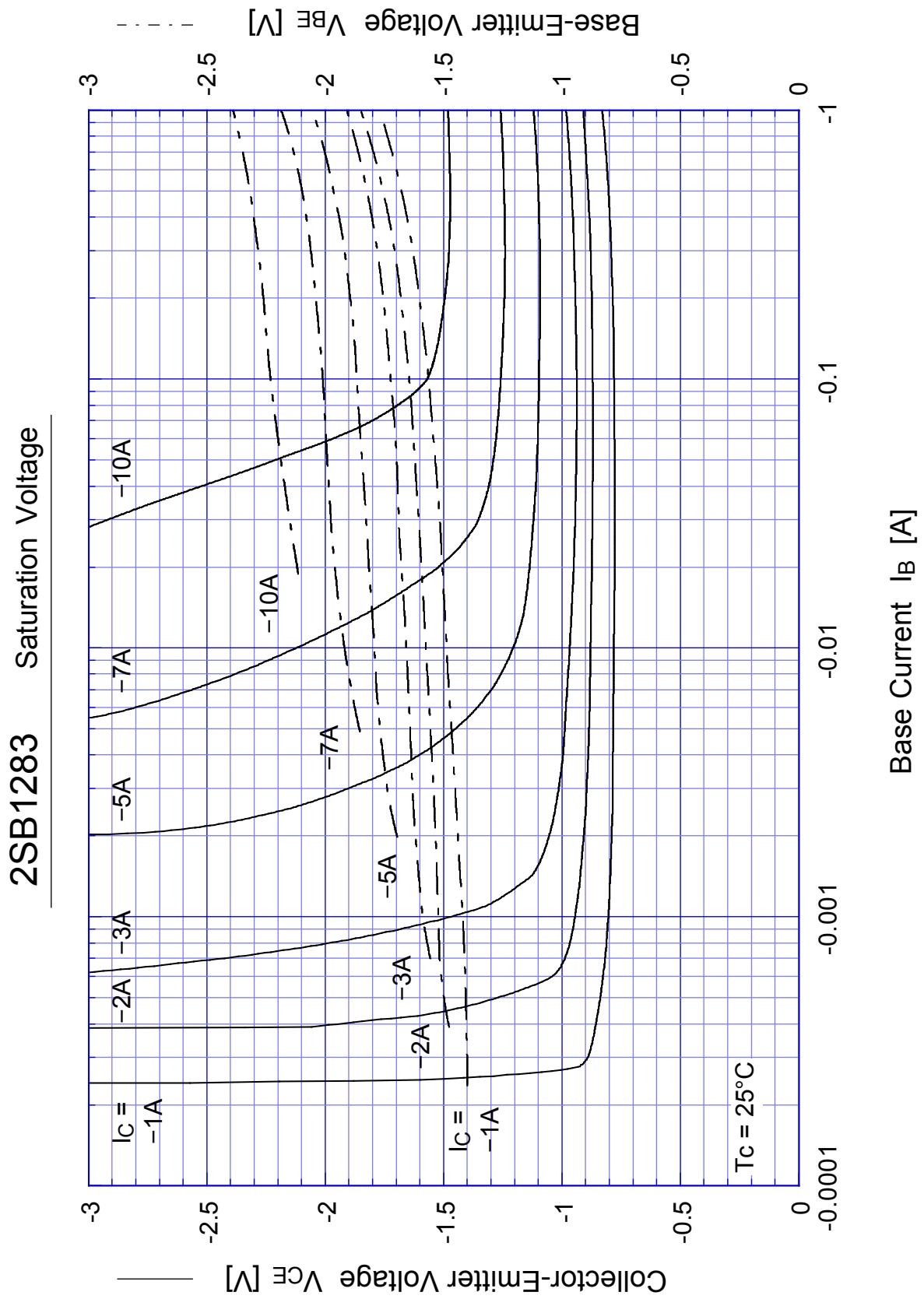
●Absolute Maximum Ratings

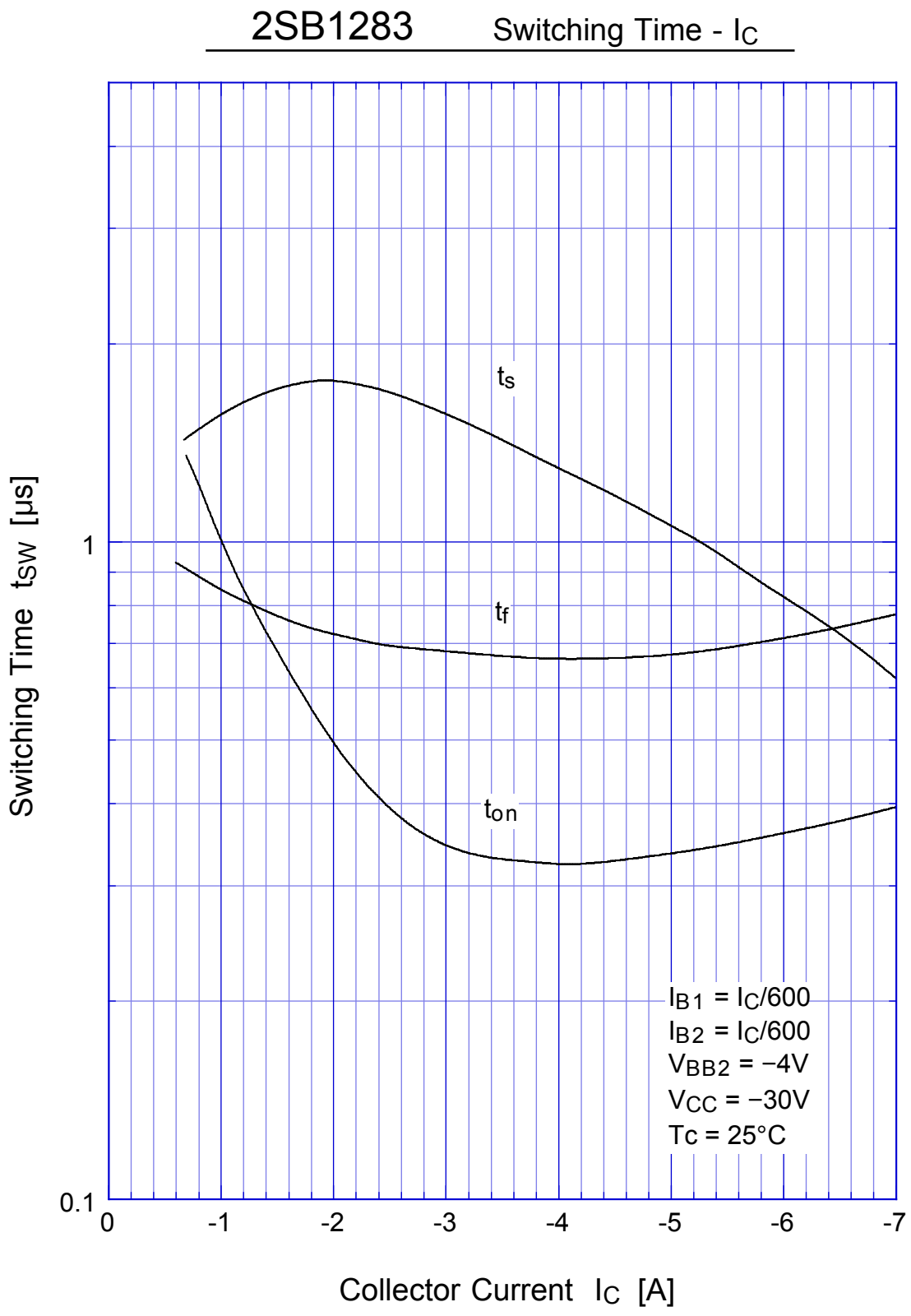
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	Tstg		-55～+150	℃
Junction Temperature	Tj		+150	℃
Collector to Base Voltage	V_{CBO}		-100	V
Collector to Emitter Voltage	V_{CEO}		-100	V
Emitter to Base Voltage	V_{EBO}		-7	V
Collector Current DC	I_C		-7	A
Collector Current Peak	I_{CP}		-10	A
Base Current DC	I_B		-0.5	A
Base Current Peak	I_{BP}		-1	A
Total Transistor Dissipation	P_T	Tc = 25℃	30	W
Dielectric Strength	Vdis	Terminals to case AC 1 minute	2	kV
Mounting Torque	TOR	(Recommended torque : 0.3N･m)	0.5	N･m

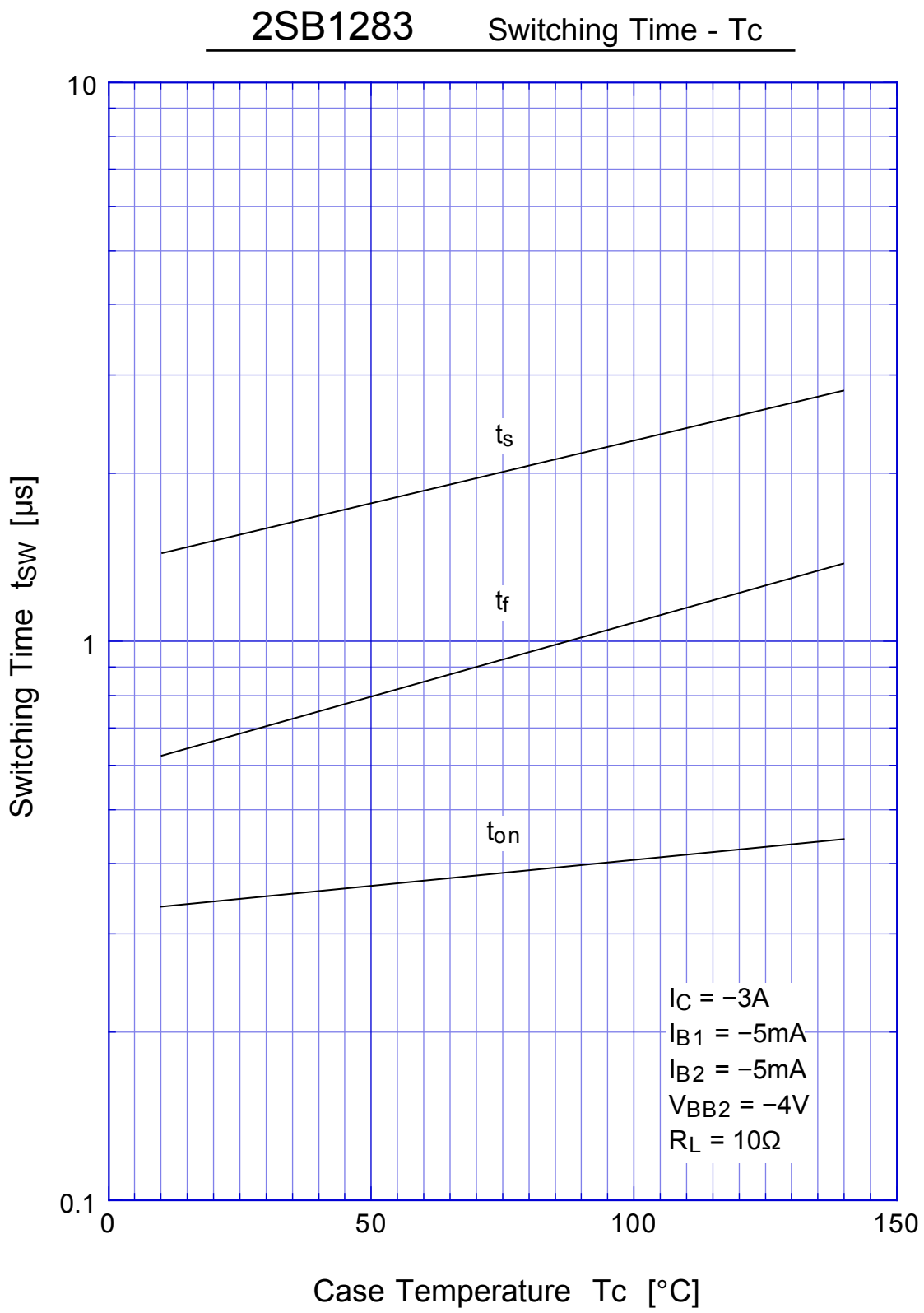
●Electrical Characteristics (Tc=25℃)

Item	Symbol	Conditions	Ratings	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = -100V	Max -0.1	mA
	I_{CEO}	V_{CE} = -100V	Max -0.1	
Emitter Cutoff Current	I_{EBO}	V_{EB} = -7V	Max -5	mA
DC Current Gain	h_{FE}	V_{CE} = -3V, I_C = -3A	Min 1,500	
			Max 15,000	
Collector to Emitter Saturation Voltage	V_{CE}(sat)	I_C = -3A	Max -1.5	V
Base to Emitter Saturation Voltage	V_{BE}(sat)	I_B = -5mA	Max -2.0	V
Thermal Resistance	θ jc	Junction to case	Max 4.16	℃/W
Transition Frequency	f_T	V_{CE} = 10V, I_C = 0.7A	TYP 20	MHz
Turn on Time	ton	I_C = -3A	Max 1	μs
Storage Time	ts	I_{B1} = I_{B2} = -5mA	Max 4	
Fall Time	tf	R_L = 10Ω V_{BB2} = -4V	Max 2	

查询"2SB1283"供应商







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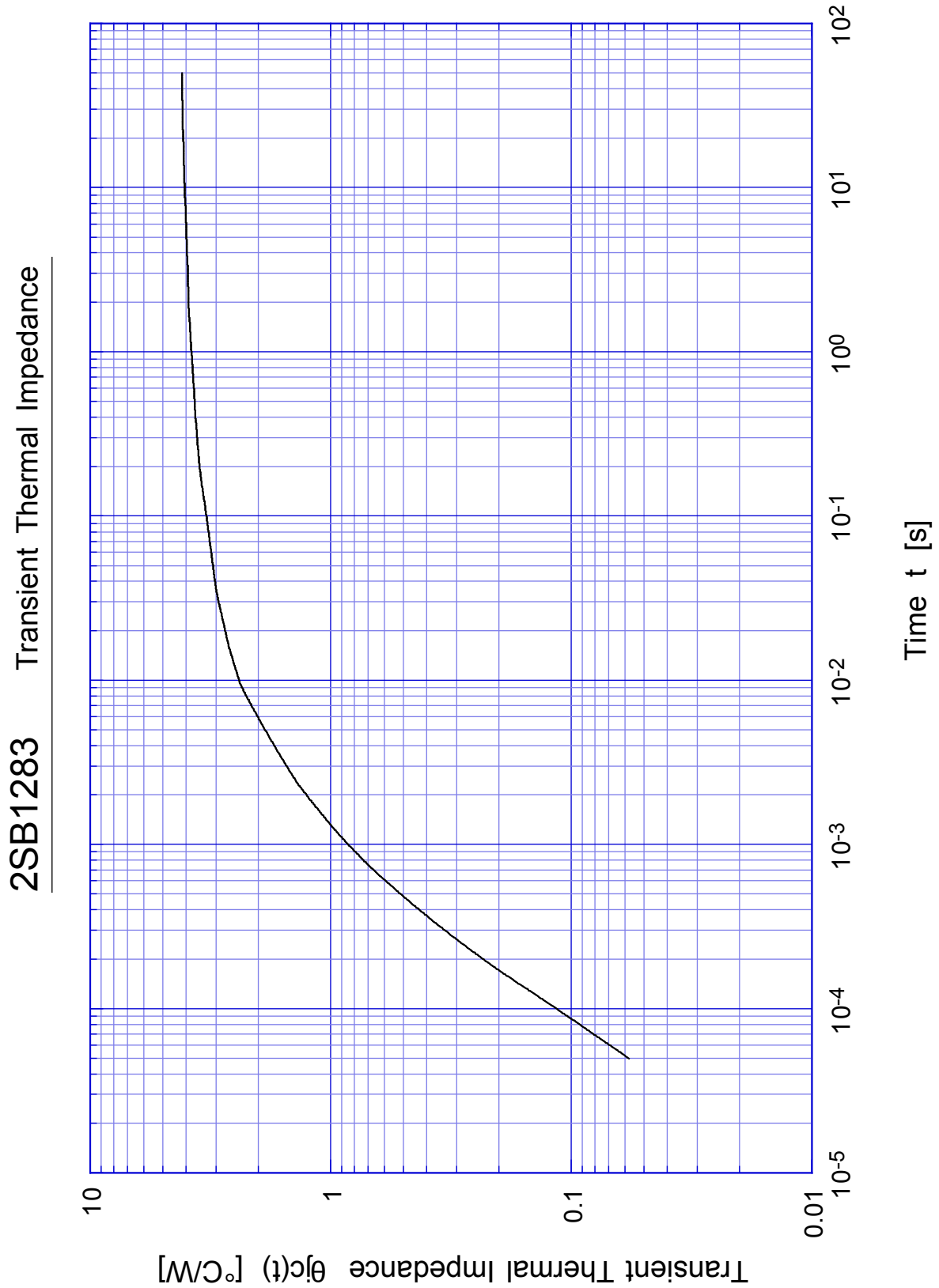

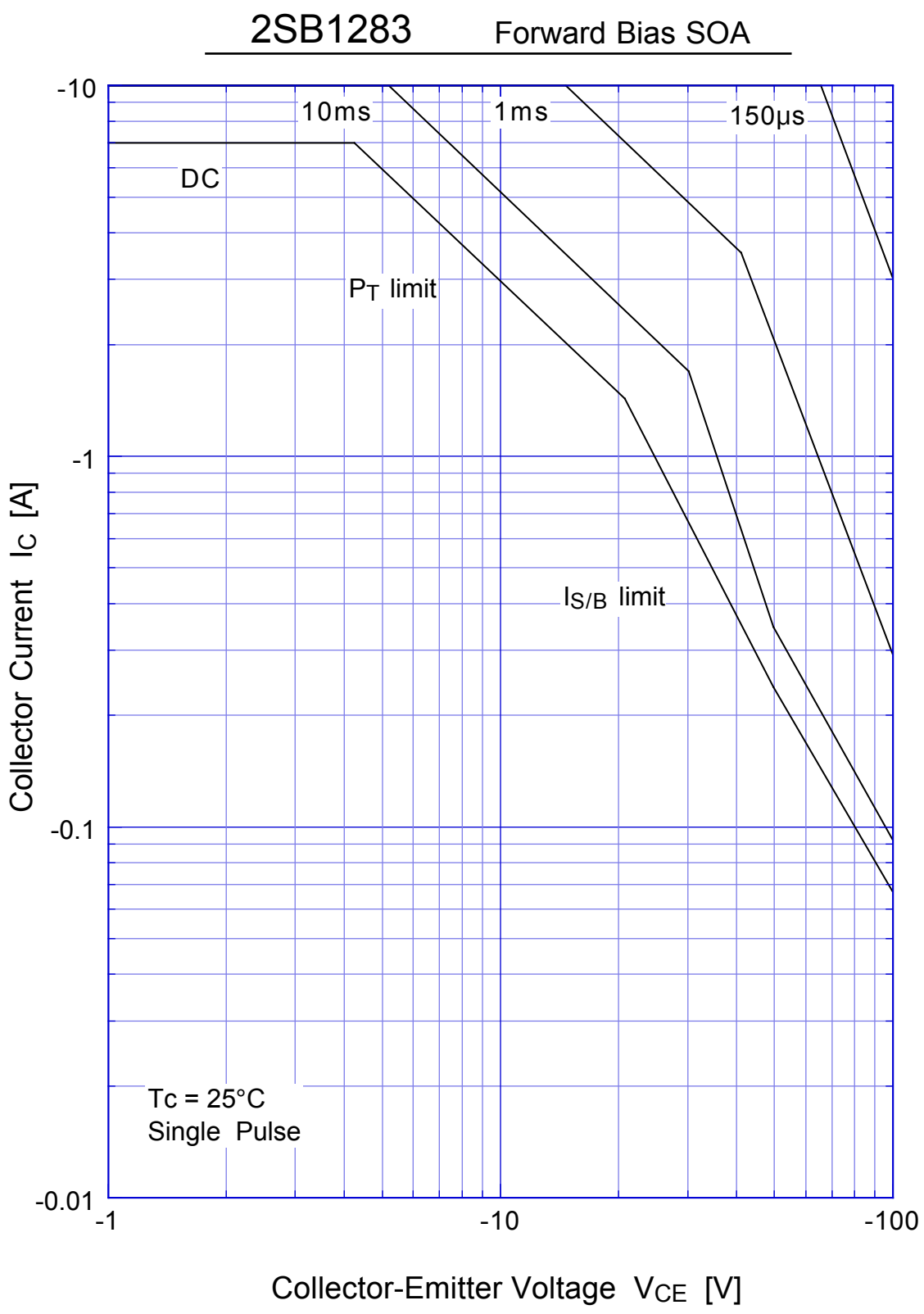

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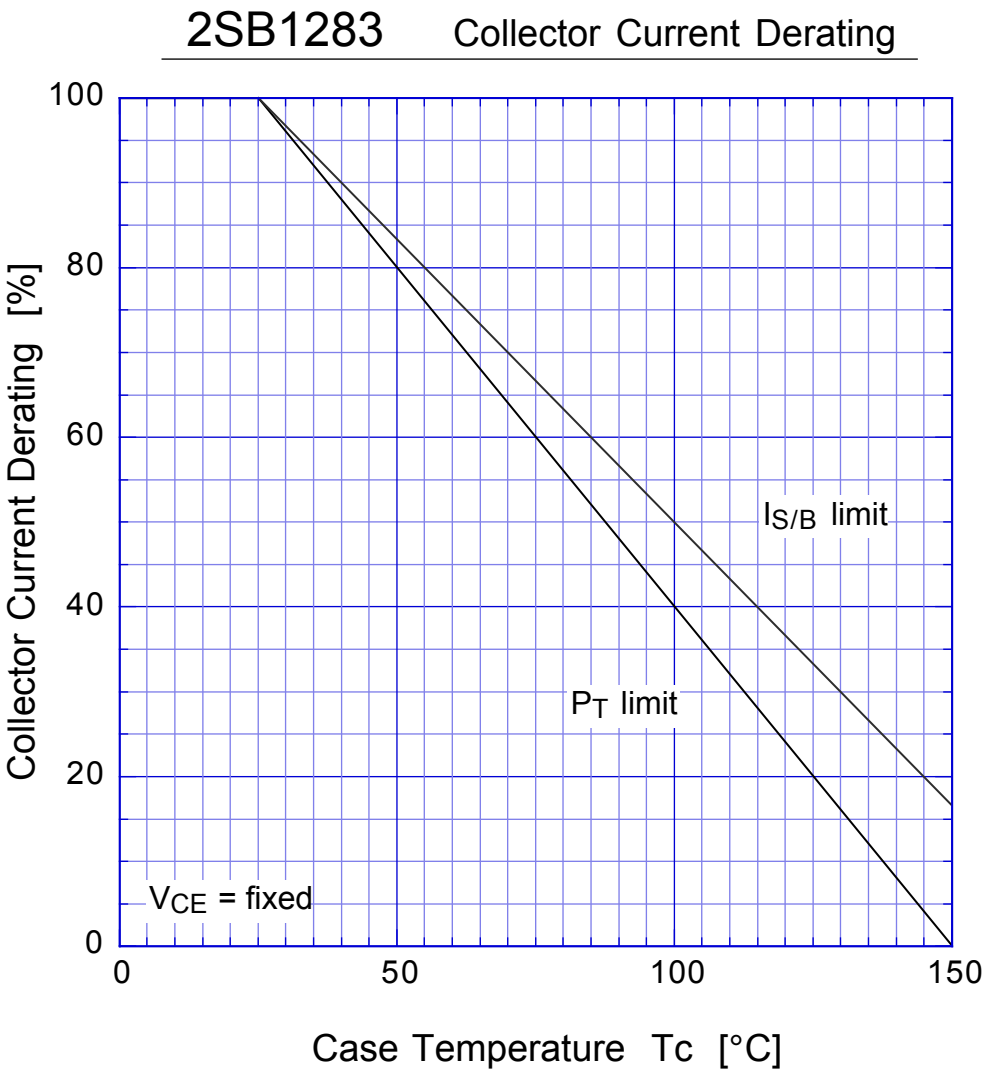

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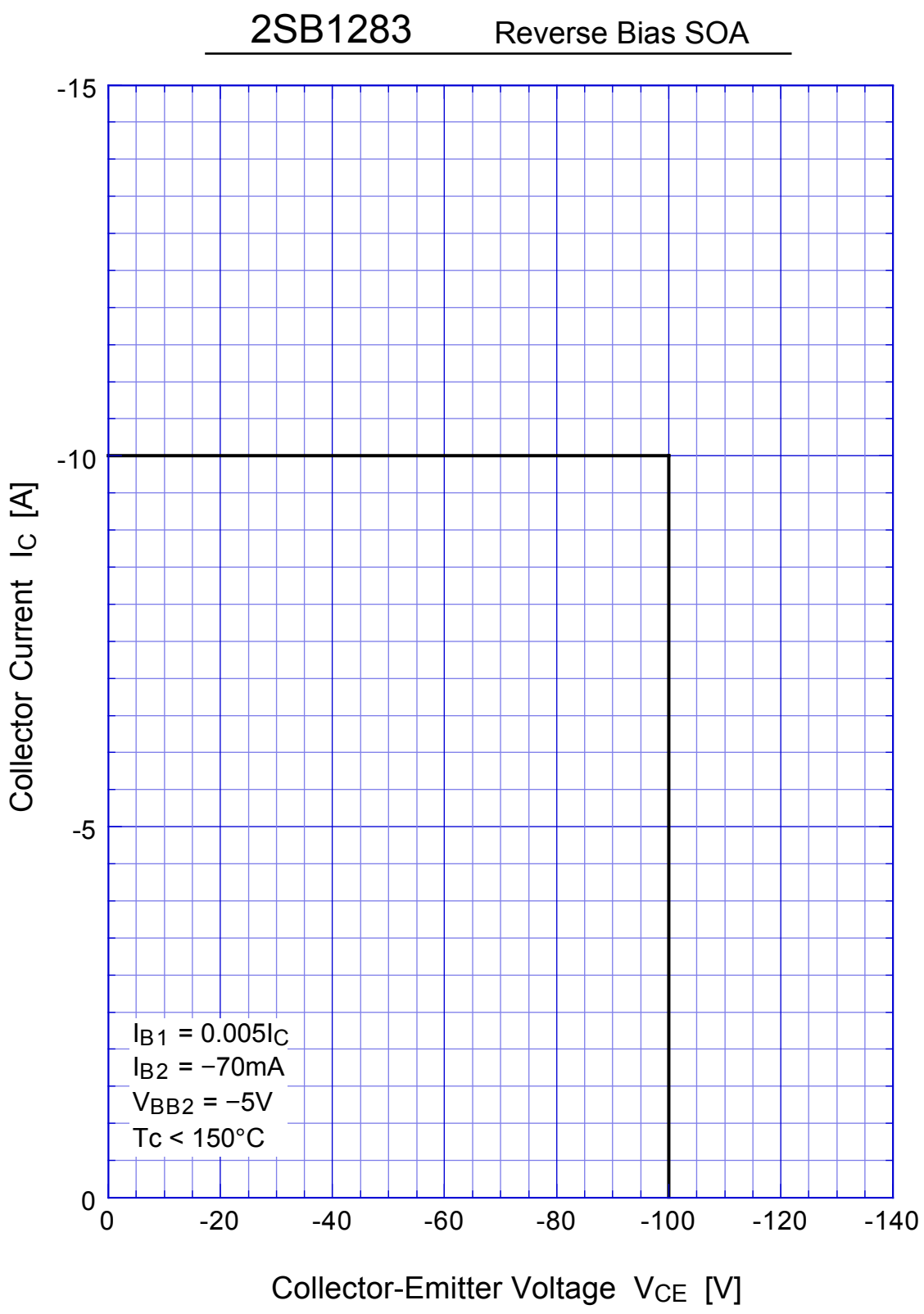

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